

Guidelines for Abstract Preparation of EDISON 18

(Bold, 12 point, Times or Times New Roman)

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Camera-ready 1-page abstract should be prepared on an A4-size paper with 2 cm margins all around. The abstract must include the title of the paper, author(s), affiliation(s), address(es) and e-mail address. Use capital letters for the initial letter of each word except articles, prepositions and conjunctions. Place a blank line between the title and author(s). The main text should be typed with single-spaced and 11 point. List and numbers of all the references should be at the end of the abstract. When referring to them in the text, the reference number should be indicated by brackets, such as [1, 2]. The deadline of the submission is **March 15, 2013**.

The 18th International Conference on Electron Dynamics in Semiconductors, Optoelectronics and Nanostructures (EDISON) will be held in Matsue, Japan, from July 22 (Monday) through 26 (Friday), 2013. Since the first meeting was held in Modena, Italy, in 1973, this series of meetings have been organized regularly; Modena, Italy (1973), Denton, USA (1977), Montpellier, France (1981), Innsbruck, Austria (1985), Boston, USA (1987), Scottsdale, USA (1989), Nara, Japan (1991), Oxford, UK (1993), Chicago, USA (1995), Berlin, Germany (1997), Kyoto, Japan (1999), Santa Fe, USA (2001), Modena, Italy (2003), Chicago, USA (2005), Tokyo, Japan (2007), Montpellier, France (2009), and Santa Barbara, USA (2011). EDISON 18 will highlight the latest progress in the field of fundamental physics and applications of electron dynamics in semiconductors, opto-electronic devices, and nanostructures.



Fig. 1. EDISON 18 logo (10 point)

The scope of EDISON 18 covers nonequilibrium and hot carrier dynamics in semiconductors, optoelectronics and nanostructure devices, with emphasis on the physics of transport and optical phenomena, including:

1. Nonequilibrium carrier transport in bulk and nanostructure systems
2. Coherent carrier dynamics in solids for quantum processing and communications
3. Coherent/incoherent carrier dynamics and ultra-fast optical phenomena
4. Terahertz interactions with semiconductors
5. Semiconductor-based spintronics
6. Carrier transport and carrier dynamics in organic materials
7. Ultrafast carrier dynamics in energy conversion processes
8. Nonequilibrium thermal transport in nanostructures and devices
9. Nonequilibrium carrier dynamics and fluctuation
10. Novel materials and devices

References

- [1] T. Ando, A. B. Fowler, and F. Stern, Rev. Mod. Phys. **54**, 437 (1982).
[2] C. Jacoboni and L. Reggiani, Rev. Mod. Phys. **55**, 645 (1983).